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NTE30046
Infrared Emitting Diode – 3mm

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Power Dissipation, P_D 135mW
Forward Current, I_F
  Continuous 80mA
  Peak (Note 1) 1A
Reverse Voltage, V_R 5V
LED Junction Temperature, T_J . . . . . +100°C
Operating Temperature Range, T_{opr} . . . . . –25° to +85°C
Storage Temperature Range, T_{stg} . . . . . –40° to +100°C
Lead Temperature (During Soldering, .062 (1.6mm) from case, 5sec max), T_L . . . . . +240°C

Note 1. Duty Ratio = 0.1%, Pulse Width = 10μs

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Viewing Angle of Half Power	2θ1/2	I_F = 50mA	–	30	–	degree
Forward Voltage	V_F	I_F = 50 mA	–	1.28	1.50	V
Reverse Current	I_R	V_R = 5.0V	–	–	10	uA
Radiant Output Power	P_O	I_F = 50 mA (Note 2)	15	30	–	mw/sr
Peak Emission Wavelength	λ_p	I_F = 50 mA	–	940	–	nm
Spectrum Width of Half Valve	$\Delta\lambda$	I_F = 50 mA	–	50	–	nm
Terminal Capacitance	C_t	V = 0, F = 1MHz	–	40	–	pF

Note 2. Tolerance: 30%, measured using Exeltron 2001.